

Solid State Devices, Inc.

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DESIGNER'S DATA SHEET

Part Number / Ordering Information 1/ SFF4393A2 Screening 2/ __ = Not Screened TX = TX Level TXV = TXV Level S = S Level Package 3/ GW = GULLWING

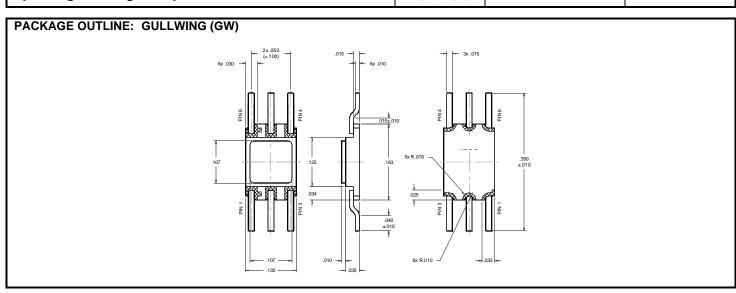
SFF4393A2GW

Dual Microminiature Package 50 mA 40 Volts Dual N-Channel JFET Transistor

Features:

- Low ON Resistance
- Low Capacitance, < 4 pF
- Fast Switching, t_{on} < 5 ns
- Used for Analog Switches, Choppers, Current Limiters, and Sample-and-Hold Applications
- TX, TXV, and S-Level Screening Available.
 Consult Factory.

Maximum Ratings	Symbol	Value	Units	
Drain – Source Voltage		V _{DS}	40	Volts
Drain – Gate Voltage		V_{DG}	40	Volts
Reverse Gate – Source Voltage		V _{SG}	40	Volts
Drain Current	I _D	50	mA	
Power Dissipation @ T _A = 25°C	Per Device Total	P _D	500 660	mW mW
Maximum Thermal Resistance	Junction to Ambient	R _{⊛JA} ^{5/}	245	°C/W
Lead Temperature (1/16" from the seated surface for 60 seconds)		T∟	300	°C
Operating & Storage Temperature		T _{OP &} T _{STG}	-65 to +200	°C







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Electrical Characteristics 4/		Symbol	Min	Max	Units
Gate – Source Breakdown Voltage	$I_G = -1\mu A, \ V_{DS} = 0 \ V$	BV _{GSS}	-40	_	Volts
Static, Drain – Source ON State Resistance	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$	r _{DS(ON)}		100	Ohms
Gate to Source Cutoff Voltage	$V_{DS} = 20 \text{ V}, I_{D} = 1 \text{ nA}$	V _{GS(OFF)} -0.5		-3.0	Volts
Gate to Source Leakage Current	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$ $V_{DG} = -20 \text{ V}, V_{DS} = 0 \text{ V}, T_A = 150^{\circ}\text{C}$	I _{GSS}		-100 -200	pA nA
Zero Gate Voltage Drain Current	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$	I _{DSS}		35	mA
Drain Cutoff Current	$V_{DS} = 20 \text{ V}, V_{GS} = -5 \text{ V}$ $V_{DS} = 20 \text{ V}, V_{GS} = -5 \text{ V}, T_A = 150^{\circ}\text{C}$	I _{D(OFF)}		100 200	pA nA
Gate to Source Forward Voltage	$I_G = 1 \text{ mA}, V_{DS} = 0 \text{ V}$	V _{GS(F)}		1.2	Volts
Drain to Source "ON" Voltage	$I_D = 3.0 \text{ mA}, V_{GS} = 0 \text{ V}$	V _{DS(ON)}		0.4	Volts
Small Signal, Drain – Source ON Resistance	$V_{GS} = 0 \text{ V}, I_{D} = 0 \text{ A}, f = 1 \text{ kHz}$	r _{ds(on)}		100	Ohms
Small Signal, Common-Source, Short-Circuit Input Capacitance	V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz	C _{iss}	_	16	pF
Small Signal, Common-Source, Short-Circuit Reverse Transfer Capacitance	$V_{DS} = 0 \text{ V}, V_{GS} = -5 \text{ V}, f = 1 \text{ MHz}$	C _{rss}	_	4.5	pF
Turn ON Delay Time	$V_{DD} = 10 \text{ V}, V_{GS (on)} = 0 \text{ V},$	t _{d (on)}		15	ns
Rise Time	$I_{D (on)} = 3.0 \text{ mA}, V_{GS (off)} = -5 \text{ V}$	t _r		5	ns
Turn OFF Delay Time	$V_{DD} = 10 \text{ V}, V_{GS (on)} = 0 \text{ V},$	t _{d (off)}	_	50	ns
Fall Time	$I_{D (on)} = 3.0 \text{ mA}, V_{GS (off)} = -5 \text{ V}$	t _f		30	ns

NOTES:

- * Pulse Test: Pulse Width = 100 μ sec, Duty Cycle = 2%
- $\underline{1}/$ For Ordering Information, Price, and Availability Contact Factory.
- 2/ Screening per MIL-PRF-19500

- 3/ For Package Outlines Contact Factory.
- 4/ Unless Otherwise Specified, All Electrical Characteristics @25°C
- 5/ Mounted on FR1 PCB

Available Part Numbers: SFF4393A2GW

PIN ASSIGNMENT							
Package	Pin 1	Pin 2	Pin 3	Pin 4	Pin 5	Pin 6	
Gullwing	Gate	Source	Drain	Gate	Source	Drain	